

LOW POWER DUAL OPERATIONAL AMPLIFIERS

AS358/358A

Pin Configuration

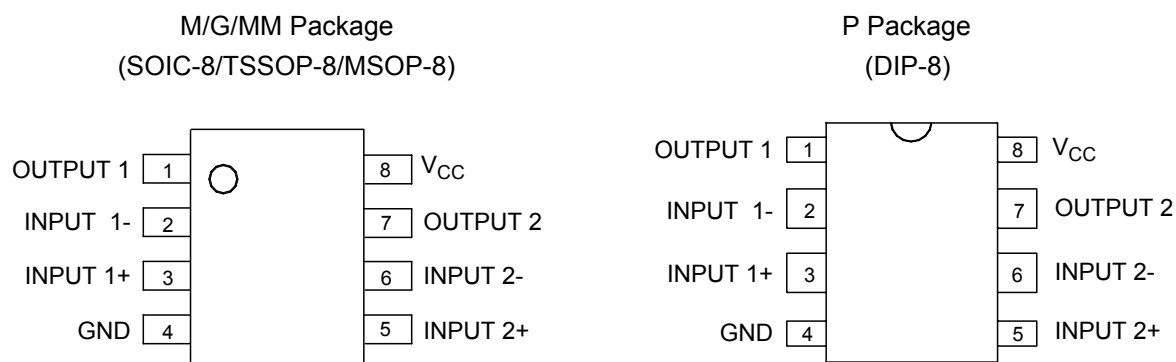


Figure 2. Pin Configuration of AS358/358A (Top View)

Functional Block Diagram

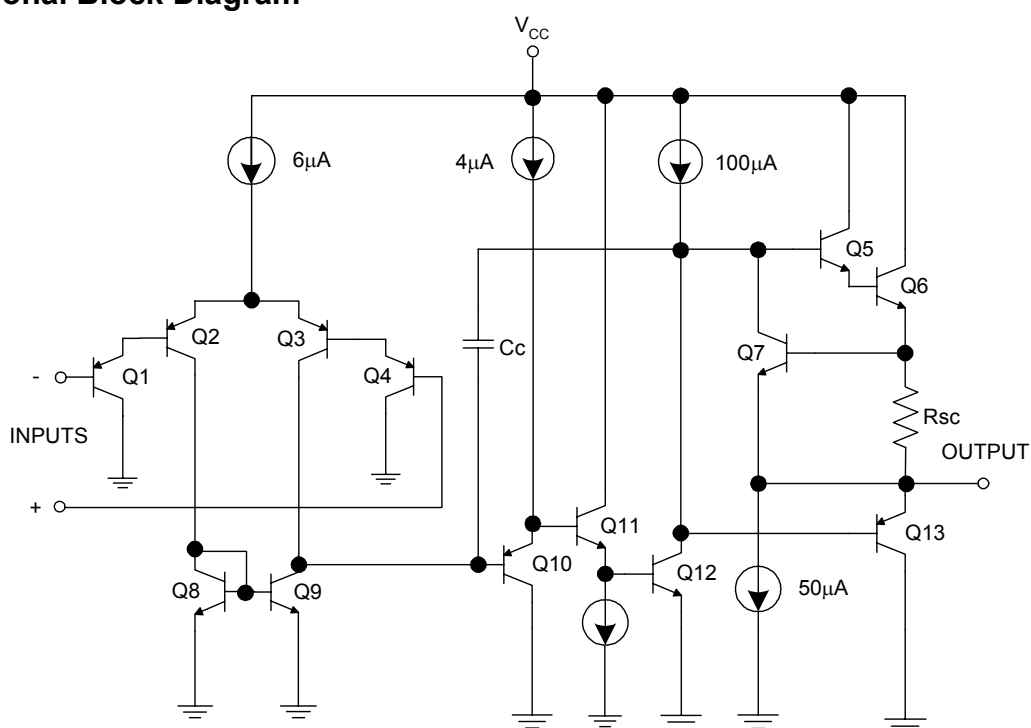


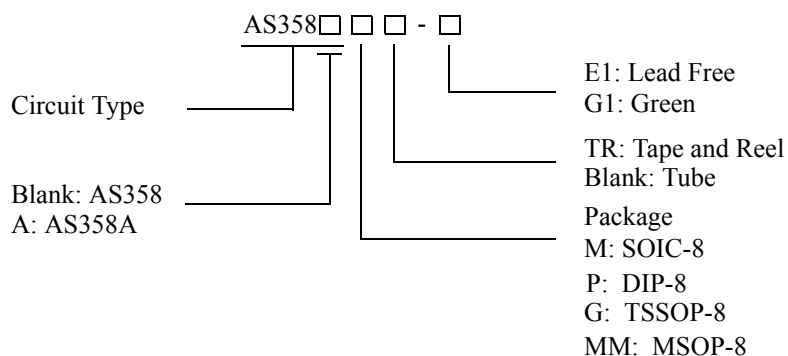
Figure 3. Functional Block Diagram of AS358/358A
(Each Amplifier)



LOW POWER DUAL OPERATIONAL AMPLIFIERS

AS358/358A

Ordering Information



Package	Temperature Range	Part Number		Marking ID		Packing Type
		Lead Free	Green	Lead Free	Green	
SOIC-8	-40 to 85°C	AS358M-E1	AS358M-G1	AS358M-E1	AS358M-G1	Tube
		AS358MTR-E1	AS358MTR-G1	AS358M-E1	AS358M-G1	Tape & Reel
		AS358AM-E1	AS358AM-G1	AS358AM-E1	AS358AM-G1	Tube
		AS358AMTR-E1	AS358AMTR-G1	AS358AM-E1	AS358AM-G1	Tape & Reel
DIP-8	-40 to 85°C	AS358P-E1	AS358P-G1	AS358P-E1	AS358P-G1	Tube
		AS358AP-E1	AS358AP-G1	AS358AP-E1	AS358AP-G1	Tube
TSSOP-8	-40 to 85°C	AS358G-E1	AS358G-G1	EG3A	GG3A	Tube
		AS358GTR-E1	AS358GTR-G1	EG3A	GG3A	Tape & Reel
MSOP-8	-40 to 85°C	AS358MM-E1	AS358MM-G1	AS358MM-E1	AS358MM-G1	Tube
		AS358MMTR-E1	AS358MMTR-G1	AS358MM-E1	AS358MM-G1	Tape & Reel

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant. Products with "G1" suffix are available in green packages.

**LOW POWER DUAL OPERATIONAL AMPLIFIERS****AS358/358A****Absolute Maximum Ratings (Note 1)**

Parameter	Symbol	Value		Unit
Power Supply Voltage	V_{CC}	40		V
Differential Input Voltage	V_{ID}	40		V
Input Voltage	V_{IC}	-0.3 to 40		V
Power Dissipation ($T_A=25^{\circ}\text{C}$)	P_D	DIP-8	830	mW
		SOIC-8	550	
		TSSOP-8	500	
		MSOP-8	470	
Operating Junction Temperature	T_J	150		$^{\circ}\text{C}$
Storage Temperature Range	T_{STG}	-65 to 150		$^{\circ}\text{C}$
Lead Temperature (Soldering, 10 Seconds)	T_{LEAD}	260		$^{\circ}\text{C}$

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit
Supply Voltage	V_{CC}	3	36	V
Ambient Operating Temperature Range	T_A	-40	85	$^{\circ}\text{C}$



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Electrical Characteristics

Limits in standard typeface are for $T_A=25^{\circ}\text{C}$, **bold** typeface applies over -40°C to 85°C (Note 2), $V_{CC}=5\text{V}$, $\text{GND}=0\text{V}$, unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Input Offset Voltage	V_{IO}	$V_O=1.4\text{V}$, $R_S=0\Omega$, $V_{CC}=5\text{V}$ to 30V		2	5	mV
					7	
				2	3	
					5	
Average Temperature Coefficient of Input Offset Voltage	$\Delta V_{IO}/\Delta T$	$T_A=-40$ to 85°C		7		$\mu\text{V}/^{\circ}\text{C}$
Input Bias Current	I_{BIAS}	I_{IN+} or I_{IN-} , $V_{CM}=0\text{V}$		20	200	nA
					200	
Input Offset Current	I_{IO}	$I_{IN+} - I_{IN-}$, $V_{CM}=0\text{V}$		5	30	nA
					100	
Input Common Mode Voltage Range (Note 3)	V_{IR}	$V_{CC}=30\text{V}$	0		$V_{CC}-1.5$	V
Supply Current	I_{CC}	$T_A=-40$ to 85°C , $R_L=\infty$, $V_{CC}=30\text{V}$		0.7	2	mA
		$T_A=-40$ to 85°C , $R_L=\infty$, $V_{CC}=5\text{V}$		0.5	1.2	
Large Signal Voltage Gain	G_V	$V_{CC}=15\text{V}$, $V_O=1\text{V}$ to 11V , $R_L \geq 2\text{k}\Omega$	85	100		dB
			80			
Common Mode Rejection Ratio	CMRR	DC, $V_{CM}=0\text{V}$ to $(V_{CC}-1.5)\text{V}$	60	70		dB
			60			
Power Supply Rejection Ratio	PSRR	$V_{CC}=5\text{V}$ to 30V	70	100		dB
			60			
Channel Separation	CS	$f=1\text{kHz}$ to 20kHz		-120		dB
Output Current	Source	I_{SOURCE} , $V_{IN+}=1\text{V}$, $V_{IN-}=0\text{V}$, $V_{CC}=15\text{V}$, $V_O=2\text{V}$	20	40		mA
			20			
	Sink	I_{SINK} , $V_{IN+}=0\text{V}$, $V_{IN-}=1\text{V}$, $V_{CC}=15\text{V}$, $V_O=2\text{V}$	10	15		mA
			5			
		$V_{IN+}=0\text{V}$, $V_{IN-}=1\text{V}$, $V_{CC}=15\text{V}$, $V_O=0.2\text{V}$	12	50		μA
Output Short Circuit Current to Ground	I_{SC}	$V_{CC}=15\text{V}$		40	60	mA
Output Voltage Swing	V_{OH}	$V_{CC}=30\text{V}$, $R_L=2\text{k}\Omega$	26			V
			26			
		$V_{CC}=30\text{V}$, $R_L=10\text{k}\Omega$	27	28		
			27			
	V_{OL}	$V_{CC}=5\text{V}$, $R_L=10\text{k}\Omega$		5	20	mV
					30	
Thermal Resistance (Junction to Case)	θ_{JC}	DIP-8		53		$^{\circ}\text{C}/\text{W}$
		SOIC-8		78		

Note 2: Limits over the full temperature are guaranteed by design, but not tested in production.

**LOW POWER DUAL OPERATIONAL AMPLIFIERS****AS358/358A****Electrical Characteristics (Continued)**

Note 3: The input common-mode voltage of either input signal voltage should not be allowed to go negatively by more than 0.3V (at 25°C). The upper end of the common-mode voltage range is $V_{CC}-1.5V$ (at 25°C), but either or both inputs can go to +36V without damages, independent of the magnitude of the V_{CC} .

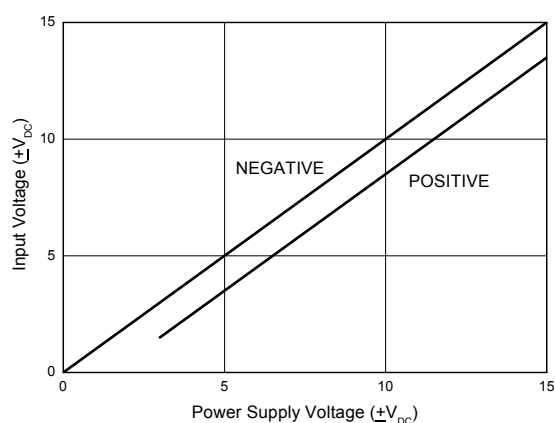
Typical Performance Characteristics

Figure 4. Input Voltage Range

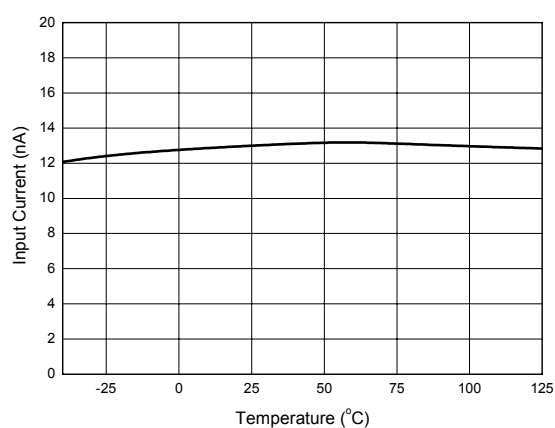


Figure 5. Input Current

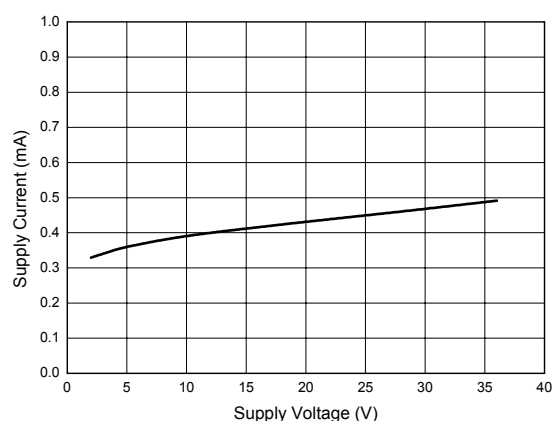


Figure 6. Supply Current

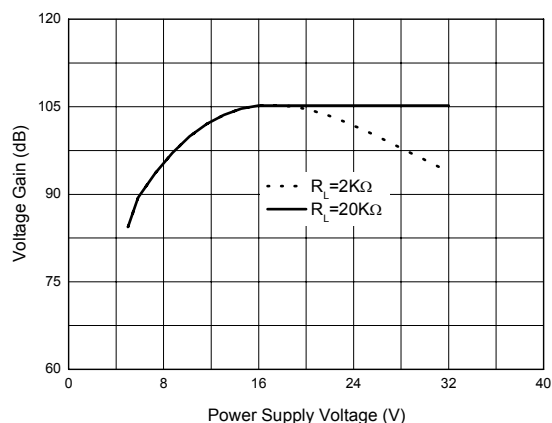


Figure 7. Voltage Gain

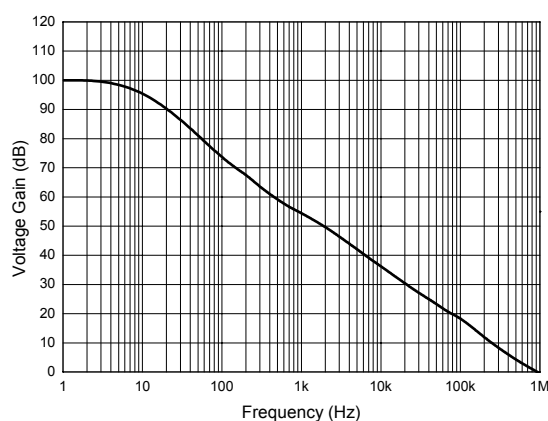
**LOW POWER DUAL OPERATIONAL AMPLIFIERS****AS358/358A****Typical Performance Characteristics (Continued)**

Figure 8. Open Loop Frequency Response

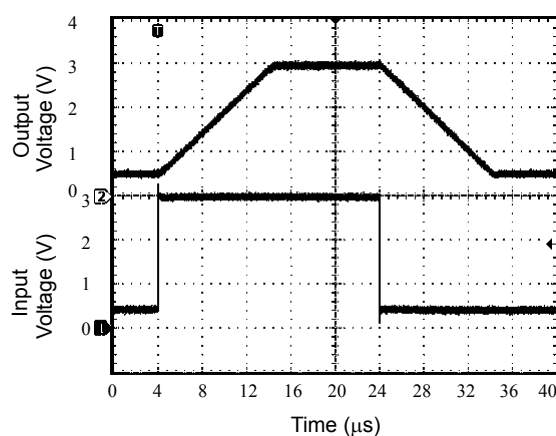


Figure 9. Voltage Follower Pulse Response

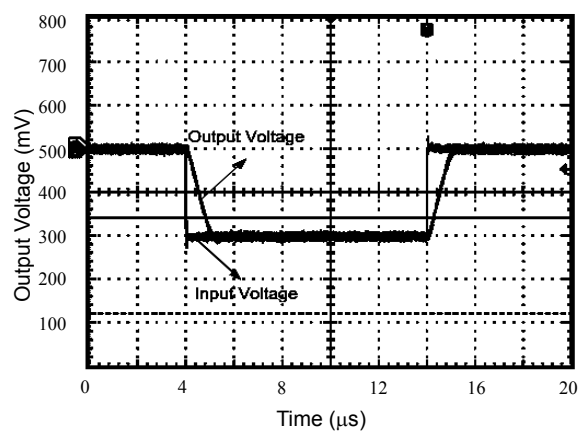
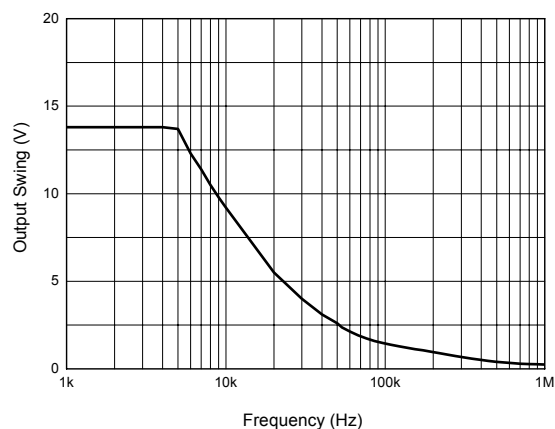
Figure 10. Voltage Follower Pulse Response
(Small Signal)

Figure 11. Large Signal Frequency Response



Typical Performance Characteristics (Continued)

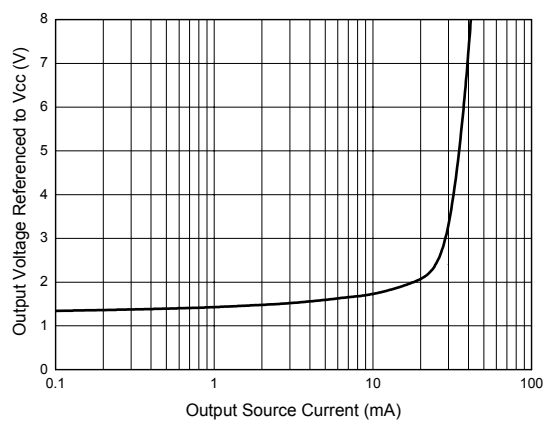


Figure 12. Output Characteristics: Current Sourcing

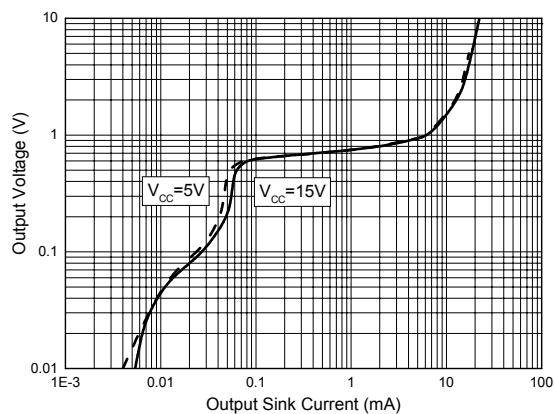


Figure 13. Output Characteristics: Current Sinking

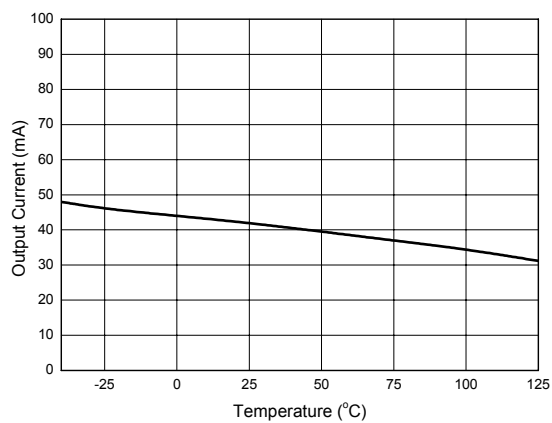


Figure 14. Current Limiting

LOW POWER DUAL OPERATIONAL AMPLIFIERS

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Typical Application

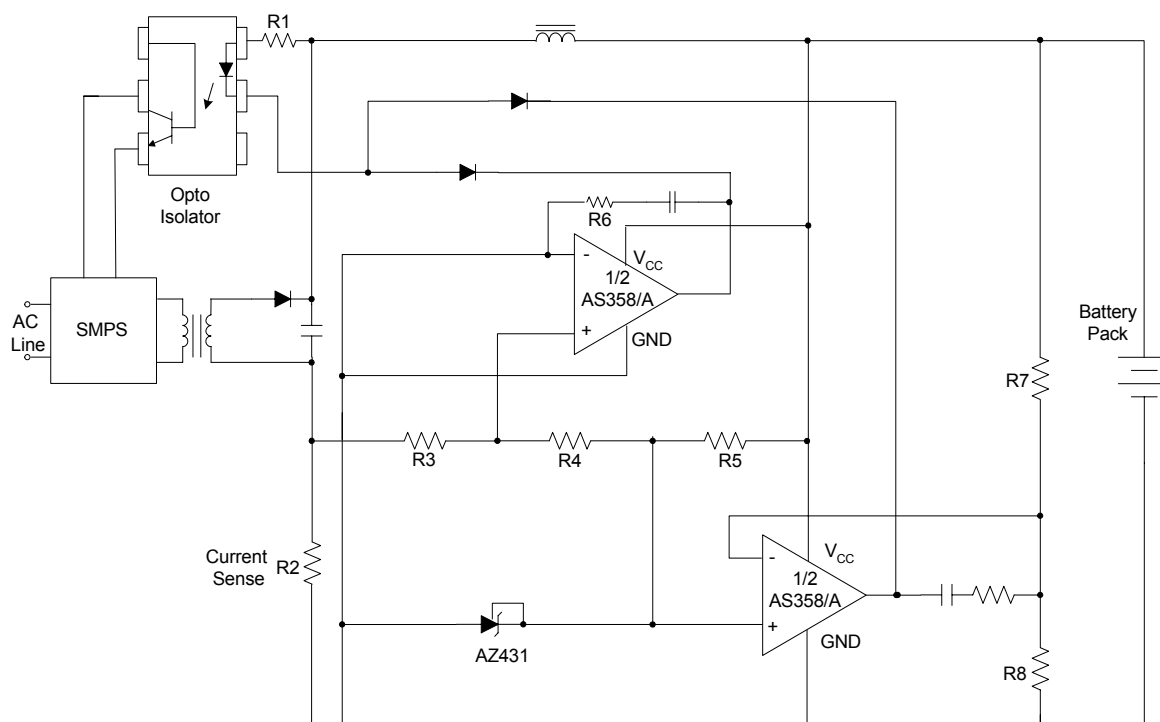


Figure 15. Battery Charger

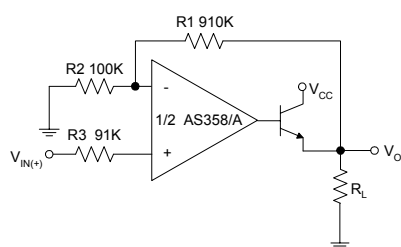


Figure 16. Power Amplifier

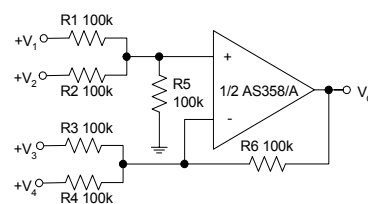


Figure 17. DC Summing Amplifier



Typical Application (Continued)

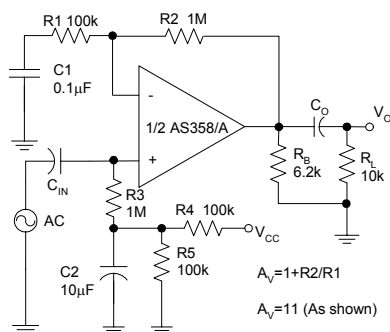


Figure 18. AC Coupled Non-Inverting Amplifier

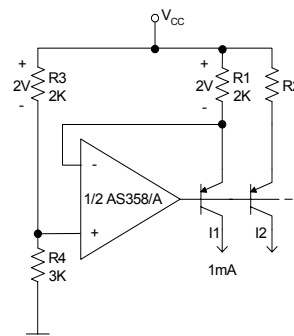


Figure 19. Fixed Current Sources

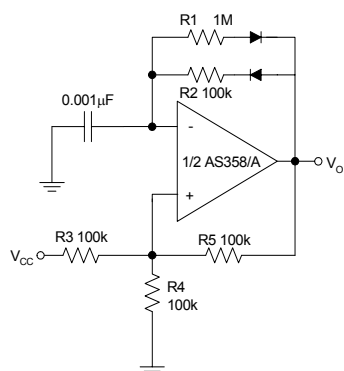


Figure 20. Pulse Generator

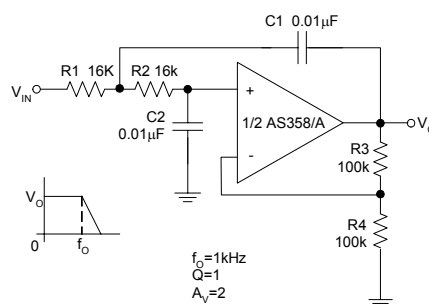
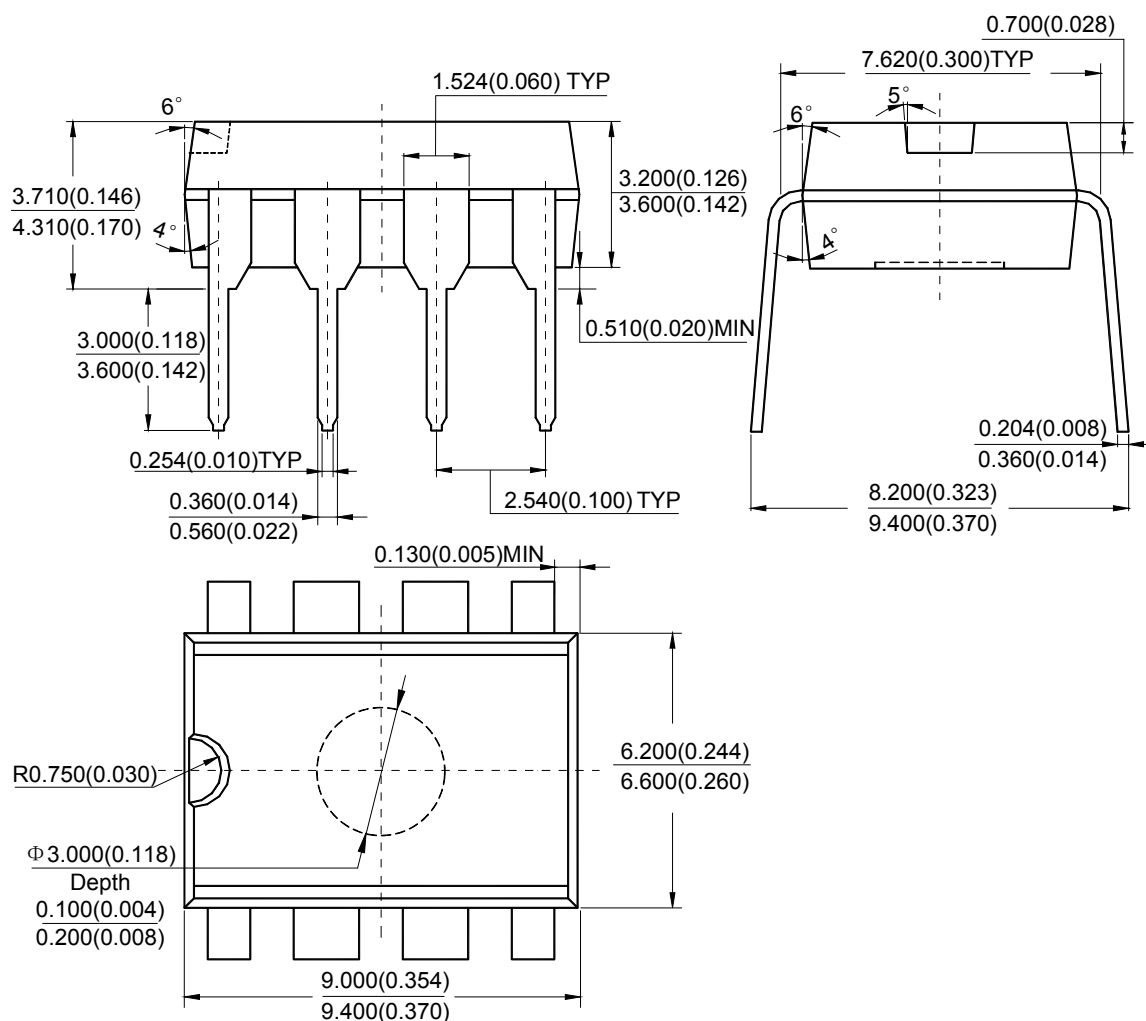
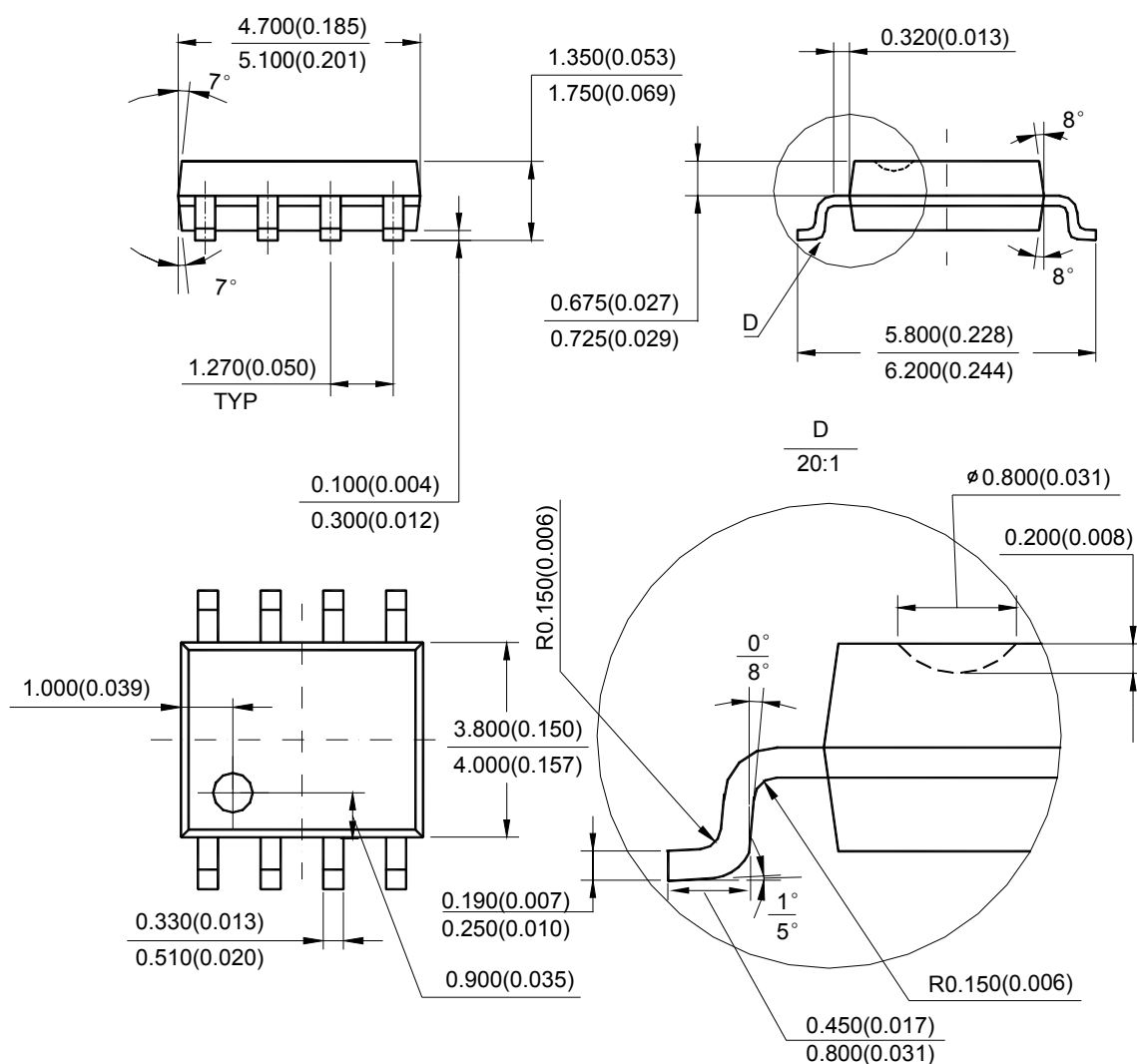


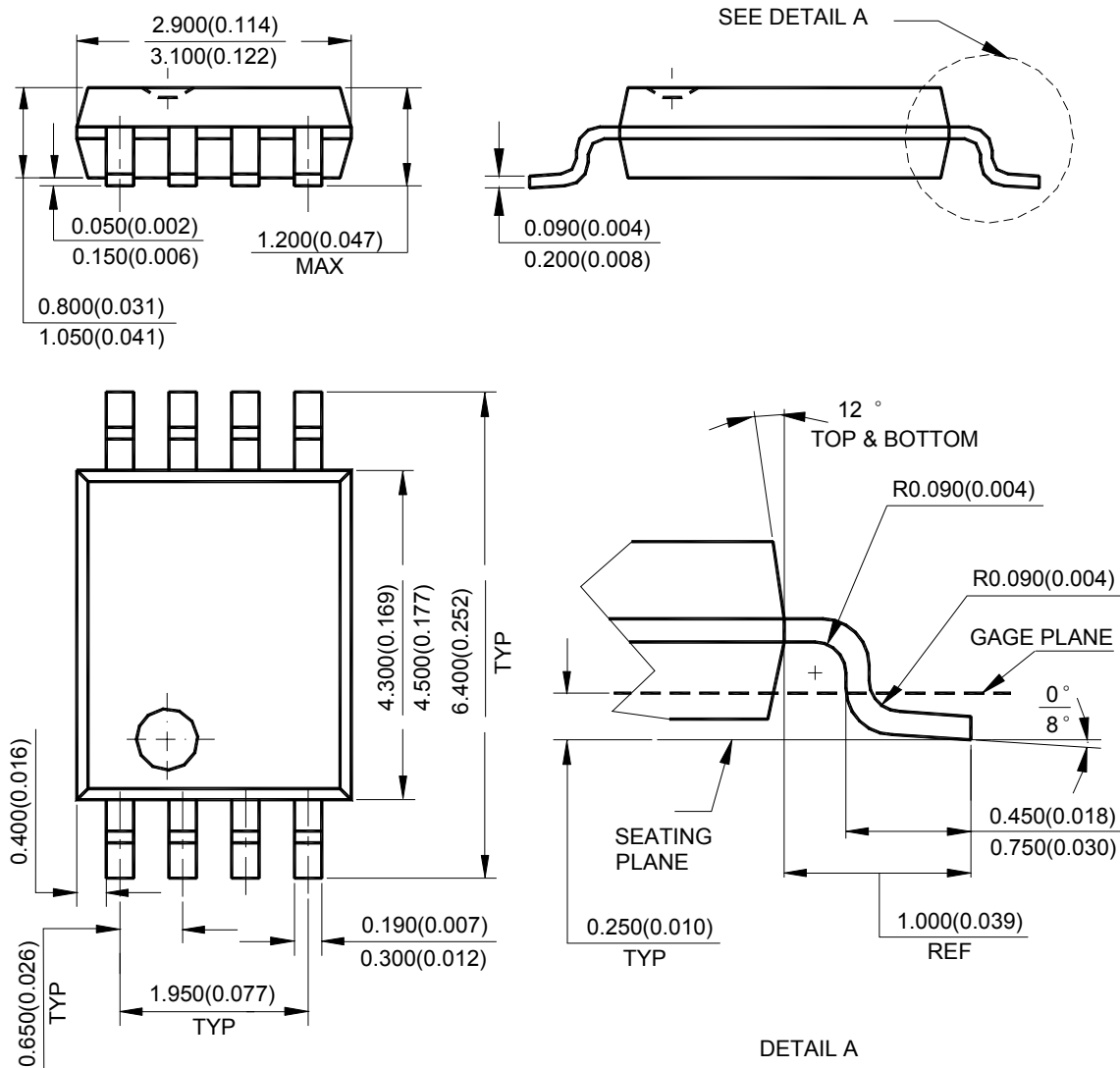
Figure 21. DC Coupled Low-Pass Active Filter

**LOW POWER DUAL OPERATIONAL AMPLIFIERS****AS358/358A****Mechanical Dimensions****DIP-8****Unit: mm(inch)**

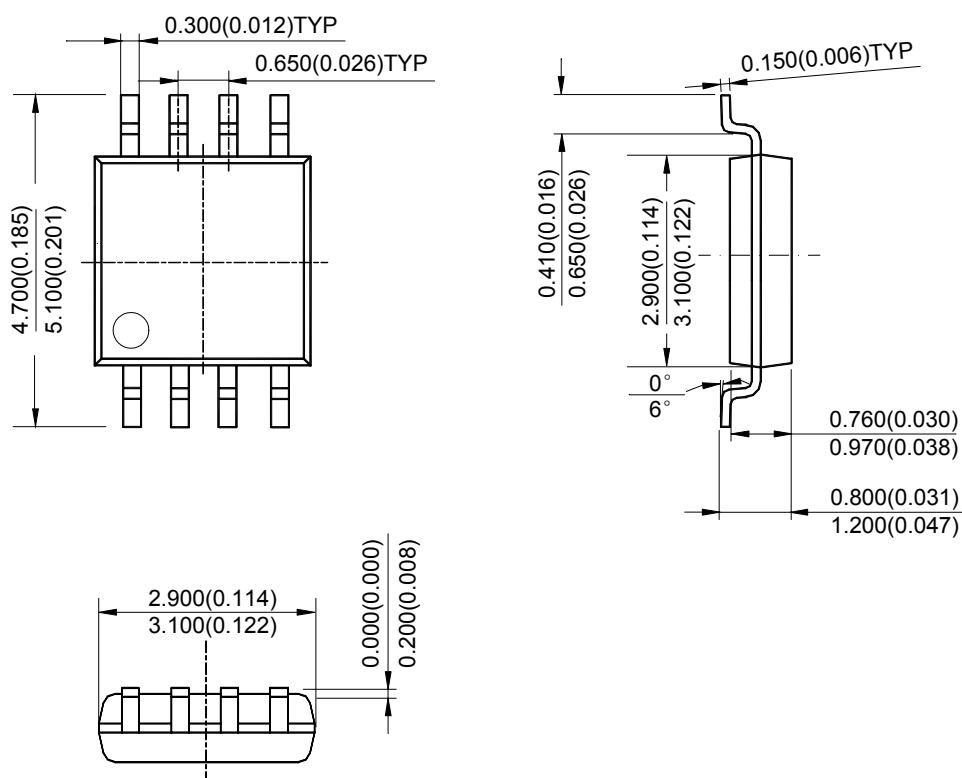
Note: Eject hole, oriented hole and mold mark is optional.

**LOW POWER DUAL OPERATIONAL AMPLIFIERS****AS358/358A****Mechanical Dimensions (Continued)****SOIC-8****Unit: mm(inch)**

Note: Eject hole, oriented hole and mold mark is optional.

**LOW POWER DUAL OPERATIONAL AMPLIFIERS****AS358/358A****Mechanical Dimensions (Continued)****TSSOP-8****Unit: mm(inch)**

Note: Eject hole, oriented hole and mold mark is optional.

**LOW POWER DUAL OPERATIONAL AMPLIFIERS****AS358/358A****Mechanical Dimensions****MSOP-8****Unit: mm(inch)**

Note: Eject hole, oriented hole and mold mark is optional.



BCD Semiconductor Manufacturing Limited

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